

GT80J101

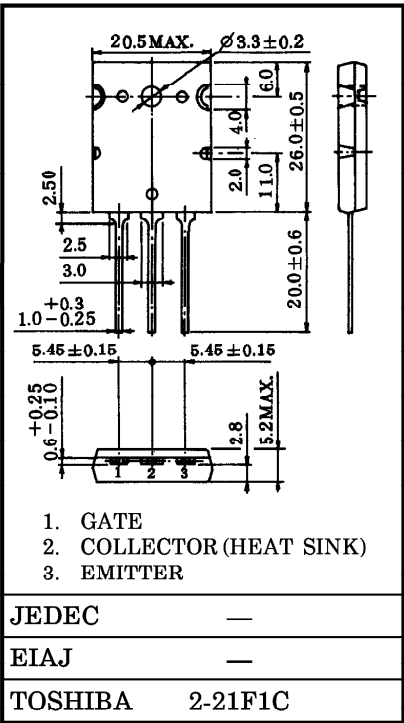
Unit in mm

HIGH POWER SWITCHING APPLICATIONS.

- High Input Impedance
- High Speed : $t_f = 0.40 \mu s$ (Max.)
- Low Saturation Voltage : $V_{CE(sat)} = 3.5V$ (Max.)
- Enhancement-Mode

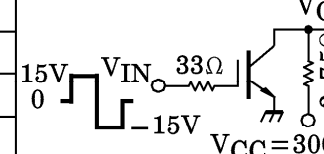
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	600	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Collector Current	DC	I_C	80	A
	1ms	I_{CP}	160	
Collector Power Dissipation (Tc = 25°C)		P_C	200	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C
Screw Torque		—	0.8	N · m



Weight : 9.75g

ELECTRICAL CHARACTERISTIC (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I _{GES}	V _{GE} =±20V, V _{CE} =0	—	—	±500	nA
Collector Cut-Off Current		I _{CES}	V _{CE} =600V, V _{GE} =0	—	—	1.0	mA
Gate-Emitter Cut-off Voltage		V _{GE(OFF)}	I _C =80mA, V _{CE} =5V	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		V _{CE(sat)} (1)	I _C =10A, V _{GE} =15V	—	—	2.0	V
		V _{CE(sat)} (2)	I _C =80A, V _{GE} =15V	—	2.5	3.5	
Input Capacitance		C _{ies}	V _{CE} =10V, V _{GE} =0, f=1MHz	—	5500	—	pF
Switching Time	Rise Time	t _r		—	0.3	0.6	μs
	Turn-on Time	t _{on}		—	0.5	0.8	
	Fall Time	t _f		—	0.25	0.40	
	Turn-off Time	t _{off}		—	0.7	1.0	
Thermal Resistance		R _{th(j-c)}		—	—	0.625	°C/W

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